Numb r	Hits	Search T xt	DB	Time stamp
84	7562	(tft r (thin near film n ar transist r)).clm.	USPAT;	2004/05/16
	1		US-P PUB	
			EPO; JPO;	20:59
			DERWENT;	
85	1159	(tft or (thin near film near transistor)).clm.	IBM_TDB	tan tan a
		and sensor	USPAT;	2004/05/16
	ļ. · .	and sellsof	US-PGPUB;	20:59
		3	EPO; JPO;	
	İ	1	DERWENT;	
86			IBM_TDB	
90	278	(tft or (thin near film near transistor)).clm.	USPAT;	2004/05/16
		and sensor.clm.	US-PGPUB;	20:59
		1.	EPO; JPO;	
			DERWENT;	
			1 7 7	
	9	(tft or (thin near film near transistor)).clm.	IBM_TDB	
		and sensor.clm. and (resistor or	USPAT;	2004/05/16
		niezorosistor or missa mai 1	US-PGPUB;	21:01
	. ,	piezoresistor or piezo-resistor).clm.	EPO; JPO;	
			DERWENT;	
8	700		IBM_TDB	
	739	(tft or (thin near film near transistor)) and	USPAT;	2004/05/16
,		sensor and (resistor or piezoresistor or	US-PGPUB:	21:01
		piezo-resistor)	EPO; JPO;	
	·		DERWENT;	•
	,		IBM_TDB	
9	363	(tft or (thin near film near transistor)) and	1	
		sensor and (resistor or piezoresistor or	USPAT;	2004/05/16
		piezo-resistor) and (beam or cantilever or	US-PGPUB;	21:01
1		diaphragm or membrane)	EPO; JPO;	
	. [	diapinagin or memprane)	DERWENT;	
D.	343	1424 143	IBM_TDB	
-	343	(tft or (thin near film near transistor)) and	USPAT;	2004/05/16
	,	sensor and (resistor or piezoresistor or	US-PGPUB;	21:01
-		piezo-resistor) and (beam or cantilever or	EPO; JPO;	v= /
		diaphragm or membrane) and (substrate or	DERWENT;	
		glass)	IBM_TDB	
	92	(tft or (thin near film near transistor)) and	USPAT;	2004/05/40
		sensor.ti,ab,clm. and (resistor or	1	2004/05/16
		piezoresistor or piezo-resistor) and (beam	US-PGPUB;	21:02
		or cantilever or diaphragm or membrane)	EPO; JPO;	
		and (substrate or glass)	DERWENT;	•
			IBM_TDB	
		(tft or (thin near film near transistor)) and		2004/05/16
1		sensor.ti,ab,clm. and (resistor or	US-PGPUB;	21:02
	1	piezoresistor or piezo-resistor) and (beam	EPO; JPO;	, .
	<u> </u> -	or cantilever or diaphragm or	DERWENT:	
1		membrane).ti,ab,clm. and (substrate or	IBM_TDB	
- 1	1.	glass)		

00				•
93		5 (tft or (thin near film near transist r)) and	USPAT;	2004/05/16
		s ns r.ti,ab, lm. and (resist r r	US-P PUB	
1		piez r sist r rpiez -r sist r).ti,ab,clm.	EPO; JPO;	,
		and (beam or cantil ver r diaphragm or	DERWENT;	
		membrane).ti,ab,clm. and (substrate or	IBM_TDB	
	1	glass)		
94		(tft or (thin near film near	USPAT;	2004/05/16
	j	transistor)).ti,ab,clm. and sensor.ti,ab,clm.	US-PGPUB:	
		and (resistor or piezoresistor or	EPO; JPO;	21:05
		piezo-resistor).ti,ab,clm. and (beam or	DERWENT;	
		cantilever or diaphragm or		
		membrane).ti,ab,clm. and (substrate or	IBM_TDB	
	1 .	glass)		
95	1813			
		transistor)).ti,ab,clm. and sensor.ti,ab,clm.	USPAT;	2004/05/16
		and sensor.ti,ab,cim.		21:05
			EPO; JPO;	
	-		DERWENT;	
96	0	(tft or (thin near film near	IBM_TDB	
		transistar)) 4: ab alamatic	USPAT;	2004/05/16
		transistor)).ti,ab,clm. and (acceleration	US-PGPUB;	21:05
		near sensor).ti,ab,clm.	EPO; JPO;	The second second
			DERWENT;	
97	2881	1484 141.	IBM_TDB	
-:	2001	(tft or (thin near film near transistor)) same	USPAT;	2004/05/16
		sensor	US-PGPUB;	21:05
			EPO; JPO;	
	-		DERWENT;	
98			IRM TOR	
, o	76	(tft or (thin near film near transistor)) same	USPAT;	2004/05/16
		sensor same (membrane or cantilever or	US-PGPUB;	21:06
	3	diaphragm or beam)	EPO; JPO;	0
			DERWENT;	
			IBM_TDB	
99	0	(tft or (thin near film near transistor)) same	USPAT;	2004/05/16
2		sensor same (membrane or cantilever or	US-PGPUB;	
		diaphragm or beam) same (resistor or	EPO; JPO;	21:06
		piezoresistor or piezo-resistor)	DERWENT;	and the second of
			'   ' '	·
00	6020	sensor and (tft or (thin near film near	IBM_TDB	2004/5-1
,		transistor))	USPAT;	2004/05/16
j			US-PGPUB;	21:11
			EPO; JPO;	
			DERWENT;	0.000
01	2385	sensor and (tft or (thin near film near	IBM_TDB	
		transistor)) and (beam or cantilever or	USPAT;	2004/05/16
1	1	diaphragm or membrane)	US-PGPUB;	21:11
			EPO; JPO;	
	,		DERWENT;	
02	363	Sangar and 1444 a. 1415	IBM_TDB	and the second s
. ]	555	sensor and (tft or (thin n ar film near		2004/05/16
. 1		transistor)) and (beam or cantil v r r		21:11
		diaphragm or m mbran ) and (resistor r	EPO; JPO;	
		piez r sistor r piezo-r sist r)	DERWENT;	
	i		IBM_TDB	·

103	103	sensor and (tft or (thin near film near	Hones	<del>1</del>
			USPAT;	2004/05/16
		transistor)) and (b am or cantilever or	US-PGPUB;	21:12
		diaphragm r m mbran ) and (resist r or	EPO; JPO;	
		pi z resist r or pi z -re istor) and	DERWENT;	
		s nsor.ti,ab,clm.	•	
104	31		IBM_TDB	
ł		sens r.ti,ab,clm. and (tft r (thin n ar film	USPAT;	2004/05/16
		near transistor)) and (beam or cantilever or	US-PGPUB;	21:12
		diaphragm or membrane).ti,ab,clm. and	EPO; JPO;	
		(resistor or piezoresistor or piezo-resistor)	DERWENT:	
		•		
105	7	sensor.ti,ab,clm. and (tft or (thin near film	IBM_TDB	
	•	near frame in the continuous film	USPAT;	2004/05/16
ŀ	1	near transistor)) and (beam or cantilever or	US-PGPUB;	21:12
	1	diaphragm or membrane).ti,ab,clm. and	EPO; JPO;	
į		(resistor or piezoresistor or	DERWENT;	
	. [	piezo-resistor).ti,ab,clm.	IBM_TDB	

L Numb r	Hi	s Search T xt	DB	Time stamp
54		7 (a c I rati n n ar sensor).clm. and	USPAT;	2004/05/16
		(piez resist r or (pi zo-r sist r)).clm.	US-PGPUB;	
			EPO; JPO;	20.00
			DERWENT;	
	1.		IBM_TDB	
55		6 (acceleration near sensor).clm. and	USPAT:	2004/05/16
		(piezoresistor or (piezo-resistor)).clm. and	US-PGPUB;	
	10.	beam.clm.	EPO; JPO;	20:30
			DERWENT;	
			IBM_TDB	
56	. (	(acceleration near sensor).clm. and		2004/07/15
	1	(piezoresistor or (piezo-resistor)).clm. and	USPAT;	2004/05/16
		beam.cim. and glass.cim.	US-PGPUB;	20:30
		g.acolonii	EPO; JPO;	
			DERWENT;	
57	1	(acceleration near sensor).clm. and	IBM_TDB	
		(piezoresistor or (piezo-resistor)).clm. and	USPAT;	2004/05/16
		beam.clm. and substrate.clm.	US-PGPUB;	20:32
		and supstrate.cim.	EPO; JPO;	
	1		DERWENT;	
58	4	(accoloration mans	IBM_TDB	
•		( ( accordation near sensor).cim. and	USPAT;	2004/05/16
		(piezoresistor or (piezo-resistor)).clm. and	US-PGPUB;	20:34
· ,		(membrane or cantilever or beam).clm. and	EPO; JPO;	
		substrate.clm.	DERWENT;	
<b>39</b>		100	IBM_TDB	
	6	("" " (""" "ear milli near transistor)) and	USPAT;	2004/05/16
•	*	(beam or cantilever or membrane) and	US-PGPUB;	20:35
		(piezoresistor or piezo-resistor)	EPO; JPO;	
* .			DERWENT;	
_			IBM_TDB	
0	6	(tft or (thin near film near transistor)) and	USPAT:	2004/05/16
	. ,	(diaphraghm or beam or cantilever or	US-PGPUB;	20:38
* .		membrane) and (piezoresistor or	EPO; JPO;	
		piezo-resistor)	DERWENT;	
_			IBM_TDB	
1	8222	(tft or (thin near film near transistor)) and	USPAT;	2004/05/40
1	•	(diaphraghm or beam or cantilever or	US-PGPUB;	2004/05/16
		membrane) and (piezoresistor or	EPO; JPO;	20:39
.		piezo-resistor or resistor or (thin near film		
		near transistor))	DERWENT;	
<b>!</b>	19	(tft or (thin near film near transistor)) and	IBM_TDB	
		(diaphraghm or beam or cantilever or	USPAT;	2004/05/16
·		membrane) and (piezoresistor or	US-PGPUB;	20:40
1		piezo-resistor or resistor or (thin near film	EPO; JPO;	•
		near transistor)) and (acceleration near	DERWENT;	
		sensor)	IBM_TDB	

63		3 (tft or (thin n ar film near	USPAT;	2004/05/16
1		transist r)).ti,ab,clm. and (diaphraghm r	US-P PUB	
		beam r cantil ver r membrane) and	EPO; JPO;	20:42
1		(piez r sistor r pi zo-resist r or resistor		
		r (thin n ar film near transist r)) and	DERWENT;	
		(accelerati n near sens r)	IBM_TDB	,
64	21			
1		film near resistor)) same (control or		2004/05/16
		controller or controlling or controlled or	US-PGPUB;	20:43
		circuit or circuitry or tft or (thin near film	EPO; JPO;	
		near transistor)) same beam	DERWENT;	
65	5	(piezoresistor or piezo-resistor or (thin near	IBM_TDB	
		film near resister) ages (and a second	,	2004/05/16
		film near resistor)) same (control or	US-PGPUB;	20:43
	1	controller or controlling or controlled or	EPO; JPO;	
		circuit or circuitry or tft or (thin near film	DERWENT;	
66	22	near transistor)) same beam same sensor	IBM_TDB	
		" Piezo-jesistor or (thin hear		2004/05/16
	1	film near resistor)) same (control or	US-PGPUB;	20:45
		controller or controlling or controlled or	EPO; JPO;	
		circuit or circuitry or tft or (thin near film	DERWENT;	
		near transistor)) same beam same sensor	IBM_TDB	
67		same (substrate or glass)		
07	0	(Prozerosistor or prezo-resistor or (thin near	USPAT;	2004/05/16
		nim near resistor)) same (control or	US-PGPUB;	20:45
**		controller or controlling or controlled or	EPO; JPO;	20170
	1	circuit or circuitry or tft or (thin near film	DERWENT;	
	1	near transistor)) same beam same sensor	IBM_TDB	
•	1	same (substrate or glass) and (tft or (thin	.5106	
		near film near transistor))		
68	6	(piezoresistor or piezo-resistor or (thin near	USPAT;	2004/05/16
		film near resistor)) same (control or	US-PGPUB;	**.
		controller or controlling or controlled or	EPO; JPO;	20:46
•		circuit or circuitry or tft or (thin near film		
		near transistor)) same beam same sensor	DERWENT;	
•	İ	same (substrate or glass) and (tft or	IBM_TDB	
•		transistor)		
69	2	(piezoresistor or piezo-resistor or (thin near		
	·	film near resistor)) same (control or	USPAT;	2004/05/16
		controller or controlling or controlled or	US-PGPUB;	20:47
		circuit or circuitry or tft or (thin near film	EPO; JPO;	
100	•	near transistor)) same beam same sensor	DERWENT;	
		Same (substrate or plant)	IBM_TDB	
		same (substrate or glass) and (tft or transistor).clm.		
70	751			
	731	(piezoresistor or piezo-resistor or (thin near	USPAT;	2004/05/16
		film near resistor)) near10 (beam or	US-PGPUB;	20:47
	.	cantilever or diaphragm or membrane)	EPO; JPO;	
			DERWENT;	
1	· · · · · · · · · · · · · · · · · · ·	namenta turin kalam vieni kanam esieni.	IBM_TDB	S
•	354	((pi zoresistor r piez -resist r or (thin		2004/05/16
		n ar film n ar resistor)) near10 (beam or		20:48
, 1	ļ	cantilever r diaphragm or	EPO; JPO;	
		membrane)).ti,ab, lm.	DERWENT;	
		· · · · · · · · · · · · · · · · · · ·		

72	111	(Injores eletin		<u> </u>
- <del>-</del>	111	W	USPAT;	2004/05/16
		near film near resistor)) n ar10 (b am or	US-P PUB;	20:48
		cantil v r or diaphragm or m mbrane)).clm	1	
			DERWENT;	
73			IBM_TDB	
J	3	Will a section biezo-tesistor of (tulu	USPAT;	2004/05/16
		near film near resistor)) near10 (beam or	US-PGPUB;	
		cantilever or diaphragm or membrane)).clm.	EPO; JPO;	
		and (acceleration near sensor).clm.	DERWENT;	
	1		IBM_TDB	
4	0	((piezoresistor or piezo-resistor or (thin	USPAT;	2004/05/16
	1	near film near resistor)) same (beam or	US-PGPUB;	
		cantilever or diaphragm or membrane)	I	20:50
	1	same (glass or substrate)).clm. and	EPO; JPO;	
		(acceleration near sensor).clm.	DERWENT;	
5	420	(alass or substrate) also and di	IBM_TDB	
	1	(glass or substrate).clm. and (beam or	USPAT;	2004/05/16
		cantilever or diaphragm or membrane).clm.	US-PGPUB;	20:52
		and (piezoresistor or piezo-resistor or (thin	EPO; JPO;	
	,	near film near transistor)).clm.	DERWENT;	
6 .			IBM_TDB	1
0	358	(glass or substrate).clm. and (beam or	USPAT;	2004/05/16
		cantilever or diaphragm or membrane).clm.	US-PGPUB;	20:52
	· ·	and (piezoresistor or piezo-resistor or (thin	EPO; JPO;	20.32
		near film near transistor)).clm. and	DERWENT;	
		(transistor or circuit or circuitry or tft).clm.		
7 -	55	(glass or substrate).clm. and (beam or	IBM_TDB	
•		cantilever or diaphragm or membrane).clm.	USPAT;	2004/05/16
	ļ	and (niezoresister or piece and it	US-PGPUB;	20:52
		and (piezoresistor or piezo-resistor or (thin	EPO; JPO;	
		near film near resistor)).clm. and (transistor	DERWENT;	
3 1	24	or circuit or circuitry or tft).clm.	IBM_TDB	
		(glass or substrate).clm. and (beam or	USPAT;	2004/05/16
		cantilever or diaphragm or membrane).clm.	US-PGPUB;	20:54
		and (piezoresistor or piezo-resistor or (thin	EPO; JPO;	,
		near film near resistor)).clm. and (transistor	DERWENT;	
	1	or circuit or circuitry or tft).clm. and	IBM_TDB	
	,	sensor.clm.		
	0	(glass or substrate).clm. and (beam or	USPAT;	2004/07/40
		cantilever or diaphragm or membrane).clm.		2004/05/16
.		and (piezoresistor or piezo-resistor or (thin	US-PGPUB;	20:54
ŀ	. ]	near film near resistor)).clm. and (transistor	EPO; JPO;	
	. [	or circuit or circuitry or tft).clm. and	DERWENT;	
		sensor.clm. and "349"	IBM_TDB	
1	-	(glass or substrate).clm. and (beam or		2004/05/16
		cantilever or diaphragm or membrane).clm.		20:55
		and (piezoresistor or piezo-resistor or (thin	EPO; JPO;	+ 7 I
		near film near resistor)).clm. and (transistor	DERWENT;	
		or circuit or circuitry or tft).clm. and	IBM_TDB	· ·
		sensor.clm. and "257"		

81	6 (glass o	r substrate).clm. and (beam r	<del></del>	<u> </u>
	cantiley	'r rdienbrown and (peam r	USPAT;	2004/05/16
1	and (nie:	r r diaphragm r m mbrane).clm.	US-PGPUB;	20:56
	near film	zor sist rorpi zo-resist r r (thin	EPO; JPO;	
	r circuit	n near resistor)). lm. and (transist r	DERWENT;	
	r circuit	t r circuitry r tft). lm. and	IBM_TDB	
•	s nsor.c	lm. and "257" and ((piezoresistor or		
	piezo-res	sistor or (thin near film near	1:	
	resistor)	) near10 (beam or cantilever or		
82	membran	ne or diaphragm)).clm.		
	2 (glass or	substrate).clm. and (beam or	USPAT;	2004/05/16
	cantileve	er or diaphragm or membrane).clm.	US-PGPUB;	20:58
	and (piez	coresistor or piezo-resistor or (thin	EPO; JPO;	
	near film	near resistor)).clm. and (transistor	DERWENT:	
	or circuit	t or circuitry or tft).clm. and	IBM_TDB	
·	sensor.cl	lm. and "257" and ((piezoresistor or		
	piezo-resi	istor or (thin near film near		
	resistor)	) near10 (beam or cantilever or		
	membran	e or diaphragm)).clm. and ((circuit		
	or circuit	ry or control or controller or		
	controllin	ng or controlled or tft or transistor)		
	same (pie	ezoresistor or piezoresistor or		
	resistor o	or (thin near film near resistor))		
	same (bea	am or cantilever or diaphragm or		
83	membrane			
03	3 (glass or s	substrate).clm. and (beam or	USPAT;	2004/05/16
	cantilever	r or diaphragm or membrane).clm.	US-PGPUB:	20:59
	and (piezo	presistor or piezo-resistor or (thin	EPO; JPO;	
	near film ı	near resistor)).clm. and (transistor	DERWENT;	
	or circuit	or circuitry or tft).clm. and	IBM_TDB	
	sensor.cin	m. and "257" and ((piezoresistor or		
	piezo-resis	stor or (thin near film near		
	resistor) o	or resistor ) near10 (beam or		
. '	cantilever	or membrane or diaphragm)).clm.		
	and ((circu	uit or circuitry or control or		
	controller	or controlling or controlled or tft		
	or transist	or) same (piezoresistor or		
	piezoresist	tor or resistor or (thin near film		
	near resist	tor)) same (beam or cantilever or		
	diaphragm	or membrane)).clm.		